

# 9A Peak Low-Side MOSFET Drivers

#### Features

- High Output Current: 9A Peak (Typical)
- Wide Operating Range: 4.5V to 18V (Typical)
- Minimum Pulse Width: 50 ns
- Latch-Up Proof: Fully Isolated Process is Inherently Immune to Any Latch-Up
- Input Will Withstand Negative Swing of Up to 5V
- High Capacitive Load Drive: 47,000 pF
- Low Delay Time: 15 ns (Typical)
- Logic High Input for Any Voltage from 2.4V to V<sub>S</sub>
- Low Equivalent Input Capacitance: 7 pF (typical)
- Low Supply Current: 500 µA (Typical)
- + Output Voltage Swing to Within 25 mV of GND or  $\rm V_S$

# Applications

- Switch Mode Power Supplies
- Motor Controls
- Pulse Transformer Driver
- Class-D Switching Amplifiers
- Line Drivers
- Driving MOSFET or IGBT Parallel Chip Modules
- Local Power On/Off Switch
- Pulse Generators

#### **General Description**

The MIC4421A and MIC4422A MOSFET drivers are rugged, efficient, and easy to use. The MIC4421A is an inverting driver, while the MIC4422A is a non-inverting driver.

Both versions are capable of 9A (peak) output and can drive the largest MOSFETs with an improved safe operating margin. The MIC4421A/4422A accepts any logic input from 2.4V to  $V_S$  without external speed-up capacitors or resistor networks. Proprietary circuits allow the input to swing negative by as much as 5V without damaging the part. Additional circuits protect against damage from electrostatic discharge.

MIC4421A/22A drivers can replace three or more discrete components, reducing PCB area requirements, simplifying product design, and reducing assembly cost.

Modern Bipolar/CMOS/DMOS construction guarantees freedom from latch-up. The rail-to-rail swing capability of CMOS/DMOS ensures adequate gate voltage to the MOSFET during power up/down sequencing. Because these devices are fabricated on a self-aligned process, they have very low crossover current, run cool, use little power, and are easy to drive.



#### Package Types

# **Typical Application Circuit**



# Functional Block Diagram



# 1.0 ELECTRICAL CHARACTERISTICS

## Absolute Maximum Ratings †

Supply Voltage (V <sub>S</sub> )	+20V
Control Input Voltage (V <sub>IN</sub> )	
Control Input Current (V <sub>IN</sub> > V <sub>S</sub> )	
Power Dissipation (T <sub>A</sub> ≤ +25°C, Note 1)	
PDIP (θ <sub>JA</sub> )	1478 mW
SOIC (0 <sub>JA</sub> )	767 mW
TO-220 (θ <sub>JA</sub> )	1756W
ESD Rating (Note 2)	

# **Operating Ratings ††**

Supply Voltage (V <sub>S</sub> )+4.5V to +18\
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**† Notice:** Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational sections of this specification is not intended. Exposure to maximum rating conditions for extended periods may affect device reliability.

**†† Notice:** The device is not guaranteed to function outside its operating ratings.

- **Note 1:** Minimum footprint.
  - **2:** Devices are ESD sensitive. Handling precautions recommended. Human body model, 1.5 k $\Omega$  in series with 100 pF.

# **ELECTRICAL CHARACTERISTICS**

**Electrical Characteristics:**  $T_A = +25^{\circ}C$  with  $4.5V \le V_S \le 18V$ , **bold** values valid for X Version:  $-55^{\circ}C \le T_A \le +125^{\circ}C$ , for Y Version:  $-40^{\circ}C \le T_A \le +85^{\circ}C$ , and for Z Version:  $0^{\circ}C \le T_A \le +70^{\circ}C$ , unless noted.

Parameter	Sym.	Min.	Тур.	Max.	Units	Conditions				
Power Supply										
Operating Input Voltage	Vs	4.5	_	18	V	—				
High Output Quiescent			0.5	1.5		V <sub>IN</sub> = 3V (MIC4422A), V <sub>IN</sub> = 0				
Current		_	_	3	mA	(MIC4421A)				
Low Output Quiescent	۱ <sub>S</sub>		50	150		V <sub>IN</sub> = 0V (MIC4422A), V <sub>IN</sub> = 3V				
Current			_	200	μA	(MIC4421A)				
Input										
Logic 1 Input Voltage	V <sub>IH</sub>	3.0	2.1	_	V	See Figure 1-3				
Logic 0 Input Voltage	VIL	—	1.5	0.8	V	See Figure 1-3				
Input Voltage Range	V <sub>IN</sub>	-5	_	V <sub>S</sub> + 0.3	V	—				
Input Current	I <sub>IN</sub>	-10	_	10	μA	$0V \le V_{IN} \le V_S$				
Output										
High Output Voltage	V <sub>OH</sub>	V <sub>S</sub> + .025	_	_	V	See Figure 1-1				
Low Output Voltage	V <sub>OL</sub>		_	0.025	V	See Figure 1-1				
Output Resistance,			0.6	1.0		-10 - 10 - 10 / (-10) / (-10				
Output High	_		_	3.6	Ω	I <sub>OUT</sub> = 10 mA, V <sub>S</sub> = 18V				
Output Resistance,	R <sub>O</sub>		0.8	1.7		-10 - 10 - 10 + 10 + 10 + 10 + 10 + 10 +				
Output Low		_	_	2.7	Ω	I <sub>OUT</sub> = 10 mA, V <sub>S</sub> = 18V				

Note 1: Guaranteed by design.

# **ELECTRICAL CHARACTERISTICS (CONTINUED)**

**Electrical Characteristics:**  $T_A = +25^{\circ}C$  with  $4.5V \le V_S \le 18V$ , **bold** values valid for X Version:  $-55^{\circ}C \le T_A \le +125^{\circ}C$ , for Y Version:  $-40^{\circ}C \le T_A \le +85^{\circ}C$ , and for Z Version:  $0^{\circ}C \le T_A \le +70^{\circ}C$ , unless noted.

Parameter	Sym.	Min.	Тур.	Max.	Units	Conditions	
Peak Output Current	I <sub>PK</sub>		9		Α	V <sub>S</sub> = 18V, See Figure 5-2	
Continuous Output Current	I <sub>DC</sub>		2		А	—	
Latch-Up Protection Withstand Reverse Current	I <sub>R</sub>	>1500	_	_	mA	Duty Cycle ≤ 2%, t ≤ 300 µs, Note 1	
Switching Time, Note 1							
Dias Time			20	75			
Rise Time	t <sub>r</sub>			120	ns	Figure 1-1, C <sub>L</sub> = 10,000 pF	
	4		24	75			
Fall Time	t <sub>f</sub>			120	ns	Figure 1-1, C <sub>L</sub> = 10,000 pF	
	4		15	68		Figure 4.4	
Delay Time	t <sub>D1</sub>		_	80	ns	Figure 1-1	
Delay Time			35	60		Figure 4.4	
	t <sub>D2</sub>			80	ns	Figure 1-1	
Minimum Input Pulse Width	t <sub>PW</sub>	_	50	_	ns	See Figure 1-1 and Figure 1-2.	
Maximum Input Frequency	f <sub>MAX</sub>	_	1	_	MHz	See Figure 1-1 and Figure 1-2.	

**Note 1:** Guaranteed by design.

#### **Test Circuits**

Note that the output pulse width may increase with input pulse widths less than 50 ns.





#### **Control Input Behavior**



FIGURE 1-3:	Input Hysteresis.
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# **TEMPERATURE SPECIFICATIONS**

Parameters	Sym.	Min.	Тур.	Max.	Units	Conditions			
Temperature Ranges									
Maximum Junction Temperature	Τ <sub>J</sub>	_	_	+150	°C	—			
Storage Temperature Range	Τ <sub>S</sub>	-65	_	+150	°C	—			
Lead Temperature	_	—	—	+300	°C	Soldering, 10 sec.			
		0	—	+70	°C	Z option			
Ambient Operating Temperature Range	T <sub>A</sub>	-40	—	+85	°C	Y option			
		-55		+125		X option			
Package Thermal Resistances									
Thermal Resistance, PDIP 8-Ld	$\theta_{JA}$	_	84.6	_	°C/W	—			
Thermal Resistance, SOIC 8-Ld	$\theta_{JA}$		163	_	°C/W	—			
Thermal Resistance, TO-220 5-Ld	$\theta_{JA}$	_	71.2	_	°C/W	—			
Thermal Resistance, PDIP 8-Ld	$\theta_{JC}$	_	41.2	_	°C/W	—			
Thermal Resistance, SOIC 8-Ld	$\theta_{JC}$	—	38.8	—	°C/W	—			
Thermal Resistance, TO-220 5-Ld	$\theta_{JC}$	_	6.5	_	°C/W	—			

**Note 1:** The maximum allowable power dissipation is a function of ambient temperature, the maximum allowable junction temperature and the thermal resistance from junction to air (i.e., T<sub>A</sub>, T<sub>J</sub>, θ<sub>JA</sub>). Exceeding the maximum allowable power dissipation will cause the device operating junction temperature to exceed the maximum +125°C rating. Sustained junction temperatures above +125°C can impact the device reliability.

#### 2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.







FIGURE 2-2: Fall Time vs. Supply Voltage.



Temperature.







FIGURE 2-5: Fall Time vs. Capacitive Load.



Supply Voltage.



**FIGURE 2-7:** Supply Current vs. Capacitive Load ( $V_S = 18V$ ).



**FIGURE 2-8:** Supply Current vs. Capacitive Load ( $V_S = 12V$ ).



**FIGURE 2-9:** Supply Current vs. Capacitive Load ( $V_S = 5V$ )



**FIGURE 2-10:** Supply Current vs. Frequency ( $V_S = 18V$ ).



**FIGURE 2-11:** Supply Current vs. Frequency ( $V_S = 12V$ ).



**FIGURE 2-12:** Supply Current vs. Frequency ( $V_S = 5V$ ).



FIGURE 2-13: Propagation Delay vs. Supply Voltage.



FIGURE 2-14: Amplitude.

Propagation Delay vs. Input



FIGURE 2-15: Propagation Delay vs. Temperature.



FIGURE 2-16: Quiescent Supply Current vs. Temperature.



FIGURE 2-17: High-State Output Resistance vs. Supply Voltage.



FIGURE 2-18: Low-State Output Resistance vs. Supply Voltage.

# 3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

Pin Number PDIP/SOIC	Pin Number TO-220	Pin Name	Description			
2	1	IN	Control Input.			
4, 5	2, 4	GND	Ground: Duplicate pins must be externally connected.			
1, 8	3, TAB	VS	Supply Input: Duplicate pins must be externally connected.			
6, 7	5	OUT	Output: Duplicate pins must be externally connected.			
3		NC	Not connected.			

TABLE 3-1: PIN FUNCTION TABLE

# 4.0 FUNCTIONAL DESCRIPTION

#### Refer to the Functional Block Diagram.

The MIC4422A is a non-inverting driver. A logic high on the IN produces gate drive output. The MIC4421A is an inverting driver. A logic low on the IN produces gate drive output. The output is used to turn on an external N-channel MOSFET.

#### 4.1 Supply

VS (supply) is rated for +4.5V to +18V. External capacitors are recommended to decouple noise.

#### 4.2 Input

IN (control) is a TTL-compatible input. IN must be forced high or low by an external signal. A floating input will cause unpredictable operation.

A high input turns on Q1, which sinks the output of the 0.1 mA and the 0.3 mA current source, forcing the input of the first inverter low.

#### 4.3 Hysteresis

The control threshold voltage, when IN is rising, is slightly higher than the control threshold voltage when CTL is falling.

When IN is low, Q2 is on, which applies the additional 0.3 mA current source to Q1. Forcing IN high turns on Q1 which must sink 0.4 mA from the two current sources. The higher current through Q1 causes a larger drain-to-source voltage drop across Q1. A slightly higher control voltage is required to pull the input of the first inverter down to its threshold.

Q2 turns off after the first inverter output goes high. This reduces the current through Q1 to 0.1 mA. The lower current reduces the drain-to-source voltage drop across Q1. A slightly lower control voltage will pull the input of the first inverter up to its threshold.

#### 4.4 Drivers

The second (optional) inverter permits the driver to be manufactured in inverting and non-inverting versions.

The last inverter functions as a driver for the output MOSFETs Q3 and Q4.

#### 4.5 Output

OUT is designed to drive a capacitive load.  $V_{OUT}$  (output voltage) is either approximately the supply voltage or approximately ground, depending on the logic state applied to IN.

If IN is high, and  $V_{\text{S}}$  (supply) drops to zero, the output will be floating (unpredictable).

# 5.0 APPLICATION INFORMATION

#### 5.1 Supply Bypassing

Charging and discharging large capacitive loads quickly requires large currents. For example, charging a 10,000 pF load to 18V in 50 ns requires 3.6A.

The MIC4421A/22A has double bonding on the supply pins, the ground pins, and output pins. This reduces parasitic lead inductance. Low inductance enables large currents to be switched rapidly. It also reduces internal ringing that can cause voltage breakdown when the driver is operated at or near the maximum rated voltage.

Internal ringing can also cause output oscillation due to feedback. This feedback is added to the input signal because it is referenced to the same ground.



FIGURE 5-1: Switching Time Due to Negative Feedback.

TABLE 5-1: MIC4421A MAX. OPERATING FREQUENCY

Vs	Maximum Frequency					
18V	220 kHz					
15V	300 kHz					
10V	640 kHz					
5V	2 MHz					
<b>Conditions:</b> θ <sub>JA</sub> = 150°C/W, T <sub>A</sub> = 25°C, C <sub>L</sub> = 10,000 pF.						

To guarantee low supply impedance over a wide frequency range, a parallel capacitor combination is recommended for supply bypassing. Low inductance ceramic disk capacitor with short lead lengths (<0.5 inch) should be used. A 1  $\mu$ F low-ESR film capacitor in parallel with two 0.1  $\mu$ F low-ESR ceramic capacitors, (such as AVX RAM Guard<sup>®</sup>), provides adequate bypassing. Connect one ceramic capacitor directly between pins 1 and 4. Connect the second ceramic capacitor directly between pins 8 and 5.

### 5.2 Grounding

The high current capability of the MIC4421A/22A demands careful PCB layout for best performance. Because the MIC4421A is an inverting driver, any ground lead impedance will appear as negative feedback which can degrade switching speed. Feedback is especially noticeable with slow rise time inputs. The MIC4421A input structure includes about 600 mV of hysteresis to ensure clean transitions and freedom from oscillation, but attention to layout is still recommended.

Figure 5-1 shows the feedback effect in detail. As the MIC4421A input begins to go positive, the output goes negative and several amperes of current flow in the ground lead. As little as  $0.05\Omega$  of PC trace resistance can produce hundreds of millivolts at the MIC4421A ground pins. If the driving logic is referenced to power ground, the effective logic input level is reduced and oscillation may result.

To ensure optimum performance, separate ground traces should be provided for the logic and power connections. Connecting the logic ground directly to the MIC4421A GND pins will ensure full logic drive to the input and ensure fast output switching. Both of the MIC4421A GND pins should, however, still be connected to power ground.

# 5.3 Input Stage

The input voltage level of the MIC4421A changes the quiescent supply current. The N-Channel MOSFET input stage transistor drives a 320  $\mu$ A current source load. With a logic "1" input, the quiescent supply current is typically 500  $\mu$ A. Logic "0" input level signals reduce quiescent current to 80  $\mu$ A typical.

The MIC4421A/22A input is designed to provide 600 mV of hysteresis. This provides clean transitions, reduces noise sensitivity, and minimizes output stage current spiking when changing states. Input voltage threshold level is approximately 1.5V, making the device TTL-compatible over the full temperature and operating supply voltage ranges. Input current is less than  $\pm 10 \ \mu$ A.

The MIC4421A can be directly driven by the TL494, SG1526/1527, SG1524, TSC170, MIC38C42, and similar switch mode power supply integrated circuits. By off-loading the power-driving duties to the MIC4421A/22A, the power supply controller can operate at lower dissipation. This can improve performance and reliability.

The input can be greater than the V<sub>S</sub> supply, however, current will flow into the input lead. The input currents can be as high as 30 mA<sub>PP</sub> (6.4 mA<sub>RMS</sub>) with the input. No damage will occur to the MIC4421A/22A, however, and it will not latch.

The input appears as a 7 pF capacitance and does not change even if the input is driven from an AC source.

#### 5.4 Power Dissipation

CMOS circuits usually permit the user to ignore power dissipation. Logic families such as 4000 and 74C have outputs that can only supply a few milliamperes of current, and even shorting outputs to ground will not force enough current to destroy the device. The MIC4421A/22A on the other hand, can source or sink several amperes and drive large capacitive loads at high frequency. The package power dissipation limit can easily be exceeded. Therefore, some attention should be given to power dissipation when driving low impedance loads and/or operating at high frequency.

The supply current vs. frequency and supply current vs. capacitive load characteristic curves aid in determining power dissipation calculations. Table 5-1 lists the maximum safe operating frequency for several power supply voltages when driving a 10,000 pF load. More accurate power dissipation figures can be obtained by summing the three dissipation sources.

Given the power dissipation in the device and the thermal resistance of the package, junction operating temperature for any ambient is easy to calculate. For example, the thermal resistance of the 8-lead plastic DIP package, from the data sheet, is  $84.6^{\circ}$ C/W. In a 25°C ambient, then, using a maximum junction temperature of 150°C, this package will dissipate 1478 mW.

Accurate power dissipation numbers can be obtained by summing the three sources of power dissipation in the device:

- · Load Power Dissipation (PL)
- Quiescent power dissipation (PQ)
- Transition power dissipation (PT)

Calculation of load power dissipation differs depending on whether the load is capacitive, resistive or inductive.

#### 5.5 Resistive Load Power Dissipation

Dissipation caused by a resistive load can be calculated as:

#### **EQUATION 5-1:**

$$P_L = I^2 \times R_O \times D$$

Where:

I = The current drawn by the load.

 $R_O$  = The output resistance of the driver when the output is high, at the power supply voltage used. D = Fraction of time the load is conducting (duty cycle).

#### 5.6 Capacitive Load Power Dissipation

Dissipation caused by a capacitive load is simply the energy placed in, or removed from, the load capacitance by the driver. The energy stored in a capacitor is described by the equation:

#### **EQUATION 5-2:**

$$E = 1/2 \times C \times V^2$$

As this energy is lost in the driver each time the load is charged or discharged, for power dissipation calculations, the 1/2 is removed. This equation also shows that it is good practice not to place more voltage in the capacitor than is necessary, because dissipation increases as the square of the voltage applied to the capacitor. For a driver with a capacitive load:

#### **EQUATION 5-3:**

$$P_L = f \times C \times V_S^2$$

Where: f = Operating frequency. C = Load capacitance.  $V_S$  = Driver supply voltage.

#### 5.7 Inductive Load Power Dissipation

For inductive loads, the situation is more complicated. For the part of the cycle in which the driver is actively forcing current into the inductor, the situation is the same as it is in the resistive case:

#### **EQUATION 5-4:**

$$P_{L1} = I^2 \times R_O \times D$$

However, in this instance, the  $R_O$  required may be either the on-resistance of the driver when its output is in the high state, or its on-resistance when the driver is in the low state. This depends on how the inductor is connected, and this is still only half the story. For the part of the cycle when the inductor is forcing current through the driver, dissipation is best described as:

#### **EQUATION 5-5:**

$$P_{L2} = I \times V_D \times (1 - D)$$

Where:

 $V_D$  = The forward voltage drop of the clamp diode in the driver (generally around 0.7V).

The two parts of the load dissipation must be summed in to produce  $P_L$ :

#### **EQUATION 5-6:**

$$P_L = P_{L1} + P_{L2}$$

#### 5.8 Quiescent Power Dissipation

Quiescent power dissipation ( $P_Q$ , as described in the input section) depends on whether the input is high or low. A low input will result in a maximum current drain (per driver) of  $\leq 0.2$  mA; logic high will result in a current drain of  $\leq 3.0$  mA.

Quiescent power can therefore be found from:

#### **EQUATION 5-7:**

$$P_{O} = V_{S} \times (D \times I_{H} + (1 - D) \times I_{L})$$

Where:

 $I_{H}$  = Quiescent current with input high.

 $I_L$  = Quiescent current with input low.

D = Fraction of time input is high (duty cycle).

V<sub>S</sub> = Power supply voltage.

## 5.9 Transition Power Dissipation

Transition power is dissipated in the driver each time its output changes state, because during the transition, for a very brief interval, both the N- and P-Channel MOSFETs in the output totem-pole are ON simultaneously, and a current is conducted through them from  $V_S$  to ground. The transition power dissipation is approximately:

#### **EQUATION 5-8:**

$$P_T = 2 \times f \times V_S \times (A \bullet s)$$

A•s is a time-current factor derived from the typical operating characteristic curve Figure 2-6.

Total power (P<sub>D</sub>) then, as previously described, is just:

#### **EQUATION 5-9:**

$$P_D = P_L + P_O + P_T$$

#### 5.10 Definitions

 $C_L$  = Load Capacitance in Farads.

D = Duty Cycle expressed as the fraction of time the input to the driver is high.

f = Operating Frequency of the driver in Hertz.

 $I_{H}$  = Power supply current drawn by a driver when both inputs are high and neither output is loaded.

 $I_L$  = Power supply current drawn by a driver when both inputs are low and neither output is loaded.

 $I_D$  = Output current from a driver in Amps.

P<sub>D</sub> = Total power dissipated in a driver in Watts.

 $P_L$  = Power dissipated in the driver due to the driver's load in Watts.

P<sub>Q</sub> = Power dissipated in a quiescent driver in Watts.

 $P_T$  = Power dissipated in a driver when the output changes states ("shoot-through current") in Watts.

R<sub>O</sub> = Output resistance of a driver in Ohms.

 $V_S$  = Power supply voltage to the IC in Volts.



FIGURE 5-2: Peak Output Current Test Circuit.

# 6.0 PACKAGING INFORMATION

#### 6.1 Package Marking Information



<ul> <li>Legend: XXX Product code or customer-specific information         <ul> <li>Y Year code (last digit of calendar year)</li> <li>YY Year code (last 2 digits of calendar year)</li> <li>WW Week code (week of January 1 is week '01')</li> <li>NNN Alphanumeric traceability code                 <ul> <li>(e3) Pb-free JEDEC<sup>®</sup> designator for Matte Tin (Sn)</li> <li>* This package is Pb-free. The Pb-free JEDEC designator ((e3)) can be found on the outer packaging for this package.</li> <li>(e3) A</li> <li>Pin one index is identified by a dot, delta up, or delta down (triangle mark).</li> </ul> </li> </ul> </li> <li>Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information. Package may or may not include the corporate logo. Underbar (_) and/or Overbar (<sup>-</sup>) symbol may not be to scale.</li> </ul>			
be carried over to the next line, thus limiting the number of available characters for customer-specific information. Package may or may not include the corporate logo.	Legend	Y YY WW NNN @3 *	Year code (last digit of calendar year) Year code (last 2 digits of calendar year) Week code (week of January 1 is week '01') Alphanumeric traceability code Pb-free JEDEC <sup>®</sup> designator for Matte Tin (Sn) This package is Pb-free. The Pb-free JEDEC designator (€3) can be found on the outer packaging for this package.
	Note:	be carried characters the corpor	d over to the next line, thus limiting the number of available s for customer-specific information. Package may or may not include rate logo.

# 8-Lead SOICN Package Outline & Recommended Land Pattern





## 8-Lead PDIP Package Outline and Recommended Land Pattern

### 5-Lead TO-220 Package Outline and Recommended Land Pattern





1. Pin 1 visual index feature may vary, but must be located within the hatched area.

2. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-036 Rev C Sheet 2 of 2

NOTES:

# APPENDIX A: REVISION HISTORY

## Revision A (March 2021)

- Converted Micrel document MIC4421A/22A to Microchip data sheet template DS20006511A.
- Minor grammatical text changes throughout.

NOTES:

# **PRODUCT IDENTIFICATION SYSTEM**

To order or obtain information, e.g., on pricing or delivery, contact your local Microchip representative or sales office.

							Example	es:			
	Device Part No.				a) MIC4421A: Inverting, 9A-Peak Low-Side MOSFET Driver, –55°C to +125°C Temperature Range						
							MIC442	1AXM-TR	8-Lead SOIC	2,500/Reel	
Device:		C4421/ C4422/	Driv	Inverting, 9A-Peak Low-Side MOSFET Driver		,		ting, 9A-Peak Low 5°C Temperature R			
	IVII	54422/		Non-Inverting, 9A-Peak Low-Side MOSFET Driver			MIC442	1AYN	8-Lead PDIP	50/Tube	
							MIC442	1AYM	8-Lead SOIC	95/Tube	
Junction	х	=		125°C, RoHS-0			MIC442	1AYM-TR	8-Lead SOIC	2,500/Reel	
Temperatu Range:	re Y Z	= =		-85°C, RoHS-Co )°C, RoHS-Com			,		ting, 9A-Peak Low- C Temperature Ran		
	N	=	8-Lead PD	סור			MIC442	1AZN	8-Lead PDIP	50/Tube	
Package:	М		8-Lead SC				MIC442	1AZM	8-Lead SOIC	95/Tube	
	Т	=	5-Lead TC	0-220			MIC442	1AZM-TR	8-Lead SOIC	2,500/Reel	
							MIC442	1AZT	5-Lead TO-220	50/Tube	
Media Type	<pre><blank>= 95/Tube (SOIC only) ledia Type:  </blank></pre>			d) MIC4422A: Non-Inverting, 9A-Peak Low-Side MOSFET Driver, –40°C to +85°C Temperature Range							
			*	. ,,			MIC442	2AYN	8-Lead PDIP	50/Tube	
							MIC442	2AYM	8-Lead SOIC	95/Tube	
							MIC442	2AYM-TR	8-Lead SOIC	2,500/Reel	
							e) MIC4422A: Non-Inverting, 9A-Peak Low-Side MOSFET Driver, 0°C to +70°C Temperature Range				
							MIC442	2AZN	8-Lead PDIP	50/Tube	
					MIC442	2AYM	8-Lead SOIC	95/Tube			
			MIC442	2AYM-TR	8-Lead SOIC	2,500/Reel					
			MIC		MIC442	2AYT	5-Lead TO-220	50/Tube			
							Note 1:	catalog pa used for o the device Sales Offic	Reel identifier only a rt number descriptio rdering purposes an package. Check wit ze for package availa Reel option.	n. This identifier is d is not printed on h your Microchip	

NOTES:

#### Note the following details of the code protection feature on Microchip devices:

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